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Citation for published version:

Attfield, JP 2018, 'Mechanisms and Materials for NTE', *Frontiers in chemistry*, vol. 6.
<https://doi.org/10.3389/fchem.2018.00371>

Digital Object Identifier (DOI):

[10.3389/fchem.2018.00371](https://doi.org/10.3389/fchem.2018.00371)

Link:

[Link to publication record in Edinburgh Research Explorer](#)

Document Version:

Peer reviewed version

Published In:

Frontiers in chemistry

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Mechanisms and Materials for NTE

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Keywords: thermal expansion, negative thermal expansion, thermal expansion coefficient, structural NTE, electronic NTE, morphological NTE

Abstract

Negative thermal expansion (NTE) upon heating is an unusual property but is observed in many materials over varying ranges of temperature. A brief review of mechanisms for NTE and prominent materials will be presented here. Broadly there are two basic mechanisms for intrinsic NTE within a homogenous solid; structural and electronic. Structural NTE is driven by transverse vibrational motion in insulating framework-type materials e.g. ZrW_2O_8 and ScF_3 . Electronic NTE results from thermal changes in electronic structure or magnetism and is often associated with phase transitions. A classic example is the Invar alloy, $\text{Fe}_{0.64}\text{Ni}_{0.36}$, but many exotic mechanisms have been discovered more recently such as colossal NTE driven by Bi–Ni charge transfer in the perovskite BiNiO_3 . In addition there are several types of NTE that result from specific sample morphologies. Several simple materials, e.g. Au, CuO, are reported to show NTE as nanoparticles but not in the bulk. Microstructural enhancements of NTE can be achieved in ceramics of materials with anisotropic thermal expansion such as beta-eucryptite and Ca_2RuO_4 , and artificial NTE metamaterials can be fabricated from engineered structures of normal (positive) thermal expansion substances.

1 Introduction

NTE (negative thermal expansion) refers to the unusual phenomenon of volume contraction upon heating. Although most materials display positive thermal expansion (PTE) on heating, NTE is found in a wide variety of substances over varying ranges of temperature. This brief review is an attempt to summarise the mechanisms and prominent materials that show NTE. Further details may be found in more substantial reviews published by other authors in recent years [1-6] and in the other papers in this special issue.

Control of thermal expansion is important for many applications from ceramic cooker hobs to housings for optical devices, with zero thermal expansion (ZTE) materials or composites of PTE and NTE components being particularly useful. Thermal expansion is quantified through the linear or volume (bulk) thermal expansion coefficients (TECs), $\alpha_L = (1/L)(dL/dT)$ and $\alpha_V = (1/V)(dV/dT)$, which respectively measure the change in length L or volume V of an object with temperature T . α_L and α_V are typically quoted in 10^{-6} K^{-1} units, equivalent to ppm (parts per million) K^{-1} or MK^{-1} . Isotropic substances such as simple liquids, glasses, polycrystalline ceramics, and cubic crystals, have the same α_L in all directions with $\alpha_V = 3\alpha_L$. ZrW_2O_8 is a famous example of a cubic NTE material [7]. However uniaxial (tetragonal, hexagonal or trigonal) crystals may have different linear

TECs α_{\parallel} and α_{\perp} parallel and perpendicular to the unique symmetry axis, respectively, and crystals with orthorhombic or lower symmetry have three different values α_1 , α_2 and α_3 in mutually perpendicular directions. The volume TEC is given by $\alpha_V = \alpha_{\parallel} + 2\alpha_{\perp}$ or $\alpha_V = \alpha_1 + \alpha_2 + \alpha_3$ and when the linear TECs are very different, such as a mix of negative and positive values, then highly anisotropic thermal expansion may be obtained. TECs of crystalline materials are usually measured by determining how unit cell lengths change with temperature from diffraction measurements. Direct strain gauge (dilatometry) measurements of crystals can also be used, and are particularly useful for ceramics and amorphous materials such as glasses. Diffraction and dilatometry expansion measurements can give different results due to the effects of microstructure, as discussed in Section 3.2.

NTE materials have negative α_V over some temperature range. Reported α_V values vary from -1 to $-1000 \times 10^{-6} \text{ K}^{-1}$, but it is also important to consider the temperature range to which the quoted α_V refers as very large negative α_V 's may result from modest volume decreases over very narrow temperature ranges at a phase transition. For this reason it is often more useful to consider the overall volume decrease; materials with $-\Delta L/L > 1\%$ and so $-\Delta V/V > 3\%$ have notably large NTE.

The thermodynamic origin of thermal expansion in solids is expressed through the relation $\alpha_V = \gamma C_V/BV$ where C_V is heat capacity at constant V , $B = -V(dp/dV)$ is the bulk modulus with p being pressure, and γ is the weighted or macroscopic Grüneisen parameter summed over values for the active phonon frequencies ω_i as $\gamma_i = -d(\ln \omega_i)/d(\ln V)$. C_V and B always take positive values, hence variations in the sign of α_V arise from corresponding variations in the sign of γ . NTE is often associated with other unusual lattice properties such as negative linear compressibility under applied pressure [6] and pressure-induced softening where dB/dp becomes negative [2].

Conventional PTE arises because γ is usually positive as a consequence of the shape of the interatomic potential for bonding between two atoms, as shown in Fig. 1. Anharmonicity in the shape of the potential leads to an increase in the average interatomic distance as higher vibrational states become more populated as temperature rises. As this pairwise potential shape applies qualitatively to all type of chemical bonding, it might appear that PTE should be a universal behaviour, but NTE can arise from two ‘escapes’ that circumvent the latter argument.

68 2 Intrinsic NTE mechanisms

69 2.1 Structural NTE

The first ‘escape’ from the universal PTE behaviour expected from the interatomic potential in Fig. 1 arises from the more complex vibrational properties of large arrays of atoms. Fig. 2 shows some of the possible motions for a chain of atoms. Longitudinal (L) vibrations in the direction of the bonds (Fig. 2(a)) tend to lengthen the chain as temperature increases through thermal expansion of the individual bonds via the anharmonicity of the interatomic potential (Fig. 1). However, transverse (T) motions perpendicular to the direction of the chain tend to shorten the chain-length as the amplitude of vibration increases with temperature (Figs. 2(b) and (c)) and so can lead to NTE. This is sometimes known as the tension or ‘guitar string’ effect. Lattice vibrations, also known as phonons, are usefully classified as optic (O) with short wavelengths and high frequencies and energies, or acoustic (A) with long wavelengths and low frequencies and energies. Transverse optic (TO) phonons like that shown in Fig. 2(b) lead to large chain shortening (NTE) but may only be excited at high temperatures in view of their high energies, whereas transverse acoustic (TA) modes that lead to more modest NTE are excited at lower temperatures. Detailed theoretical and experimental analyses

83 of phonon spectra are needed to assess the contributions of TO and TA vibrations to the NTE of real
84 materials [2,6].

85 Structural NTE results when the shortening effects of the transverse phonon amplitudes due to
86 bending or torsional motions outweigh the expansion effects of the longitudinal modes. Low atomic
87 connectivity so that atoms have free space to move into during transverse motions leading to large
88 amplitudes is a necessary feature for NTE to prevail. Planar 3-coordination is the maximum
89 connectivity known to lead to negative expansion, as exemplified by graphene sheets of carbon
90 atoms [8]. However when these sheets are stacked in the three-dimensional lattice of graphite,
91 conventional PTE arising from soft van der Waals bonding potentials in the stacking (high
92 symmetry) direction gives a large $\alpha_{\parallel} = 23.1 \times 10^{-6} \text{ K}^{-1}$ that outweighs the NTE in the perpendicular
93 directions ($\alpha_{\perp} = -0.6 \times 10^{-6} \text{ K}^{-1}$) leading to bulk PTE ($\alpha_V = \alpha_{\parallel} + 2\alpha_{\perp} = 21.9 \times 10^{-6} \text{ K}^{-1}$) [9].

94 Bulk structural NTE requires a large proportion of 2-coordinate linker groups, connecting more
95 highly-coordinated atoms into a three-dimensional structure. Some representative examples of
96 structural NTE material types, with 2-connected linkers underlined, are $\text{Sc}\underline{\text{F}}_3$, $\underline{\text{A}}\text{g}_2\text{O}$, $\text{ZrW}_2\underline{\text{O}}_8$,
97 $\text{ZrV}_2\underline{\text{O}}_7$, $\text{LiAlSi}\underline{\text{O}}_4$ (the mineral β -eucryptite), zeolitic forms of $\text{Si}\underline{\text{O}}_2$ (e.g. ITQ-4) and related AlPO_4
98 (e.g. AlPO_4 -17) frameworks, $\text{Cd}(\underline{\text{C}}\text{N})_2$, $\text{Co}_3[\text{Co}(\underline{\text{C}}\text{N})_6]_2$, and metal organic frameworks such as
99 IRMOF-1 ($\text{Zn}_4\text{O}(\underline{\text{b}}\text{dc})_3$, where bdc is 1,4-benzodicycarboxylate). These have α_V values of magnitude
100 -20 to $-120 \times 10^{-6} \text{ K}^{-1}$ over typical temperature ranges of a few hundred K; details and citations are
101 shown in [2]. All of these materials have the majority of their atoms in the 2-connected linkers. The
102 metal fluoride and oxide examples have 2-coordinate atoms linking tetrahedral or octahedral units
103 together. These polyhedra tend to be rigid so the transverse vibrations of the lattice may be described
104 in the rigid unit mode (RUM) picture [2].

105 The importance of the transverse motions of the linker atoms or groups to NTE is further
106 demonstrated by changes observed when additional molecules or ions are inserted into NTE
107 materials. The inserted species within cavities in the structure are adjacent to the linkers and so
108 reduce the amplitudes of their transverse vibrations. Redox insertion of only 6% Li into Fe-doped
109 ScF_3 switches the TEC from negative to positive [10], and the same change is found when K^+ or H_2O
110 is inserted into the channels of the cyanide framework material $\text{YFe}(\text{CN})_6$ [11].

111 2.2 Electronic NTE

112 A disparate group of materials, usually dense metal alloys or ceramics, display NTE that is not driven
113 by the structural (transverse vibration) mechanism. Although they have a wide variety of physical
114 properties, and so are sometimes described as having different NTE mechanisms, they have the
115 common feature that NTE results from thermal changes in the interatomic bonding potential, as
116 illustrated in Fig. 3. Changes in bonding with temperature such that the interatomic potential
117 becomes more strongly bonding can shift the curve to a smaller equilibrium distance at higher
118 temperature. This may occur through a relatively sharp first order phase transition between two
119 distinct states, or the potential may gradually evolve with changing temperature through a second or
120 higher order transition. When the effect of this ‘escape’ outweighs the usual PTE from the
121 anharmonicity of the potentials then NTE may be observed over temperature range of the crossover.

122 Fig. 4 illustrates the schematic changes in lattice volume with temperature for a material displaying
123 electronic NTE. Both the larger-volume low- T and the smaller-volume high- T states shown in Fig. 3
124 display conventional PTE behaviour, but the change between them in the crossover region with lower
125 and upper temperatures T_l and T_u leads to NTE. T_u often marks an ordering temperature such as a
126 magnetic or ferroelectric Curie transition, and the lower limit T_l is reached where the order parameter
127 (magnetisation or electric polarisation) is fully saturated. In other cases such as charge transfer

128 materials, T_l and T_u mark the lower and upper limits of the two-phase region where the low- T and
 129 high- T phases coexist. The electronically-induced excess volume ΔV_{ex} relative to the extrapolated
 130 volume of the high- T state, V_{HT} , may be used to calculate the spontaneous volume striction $\Delta V_{\text{ex}}/V_{\text{HT}}$.
 131 Variations in the magnitude of ΔV_{ex} and the separation between T_l and T_u may be used to tune
 132 electronic materials from reduced PTE, through ZTE to NTE behaviour. A famous material that
 133 launched the study of unusual thermal expansion properties is the Invar alloy $\text{Fe}_{0.64}\text{Ni}_{0.36}$ named for
 134 an *invariant* length with a very small $\alpha_L = 1 \times 10^{-6} \text{ K}^{-1}$ (effectively ZTE) below magnetic $T_C = 500 \text{ K}$.

135 The transitions or changes that give rise to electronic NTE are usually associated with an increase in
 136 electron delocalisation on passing from the low- T to the high- T phase. The low- T phase is more
 137 electron localised or correlated (e.g. magnetically ordered), due to electron-electron repulsions that
 138 may be described by the Hubbard U energy, while the more electron delocalised or disordered high- T
 139 phase is stabilised by entropy. Electrons near the Fermi level are often in d- or f-states that are non-
 140 bonding or weakly antibonding, so their delocalisation allows the bonding potential to become more
 141 negative and shift to shorter distance as shown in Fig. 3.

142 Classes of materials where electronic NTE is found are;

- 143 • Metallic magnets, notably the Invar alloy above, also R_2Fe_{17} (R = rare earth) and related
 144 intermetallics, the permanent magnet family $\text{R}_2\text{Fe}_{14}\text{B}$, the $\text{Mn}_3(\text{Cu},\text{Ge})\text{N}$ antiperovskites, and
 145 metallic perovskite oxides SrRuO_3 and manganites such as $\text{La}_{0.8}\text{Ba}_{0.2}\text{MnO}_3$. NTE is usually
 146 observed over a wide temperature range below the magnetic Curie transition.
- 147 • Insulating magnets – these generally do not show NTE but some examples are found for
 148 frustrated spinels e.g. CdCr_2O_4 and CdCr_2S_4 , the multiferroic $\text{Pb}(\text{Fe}_{0.5}\text{Nb}_{0.5})\text{O}_3$, and orbitally
 149 ordered MnF_3 below their Curie or Néel temperatures.
- 150 • Charge transfer materials, e.g. $\text{Bi}_{0.95}\text{La}_{0.05}\text{NiO}_3$, $\text{LaCu}_3\text{Fe}_4\text{O}_{12}$, $\text{Sm}_{0.67}\text{Y}_{0.33}\text{S}$, $\text{Sm}_{2.75}\text{C}_{60}$, and
 151 $\text{Yb}_8\text{Ge}_3\text{Sb}_5$, can show very large NTE resulting from volume collapses at metal to insulator
 152 charge transfer transitions. $\text{Bi}_{0.95}\text{La}_{0.05}\text{NiO}_3$ has $\alpha_V = -410 \times 10^{-6} \text{ K}^{-1}$ between 300 and 370
 153 K, termed colossal NTE (CNTE). The oxides have intermetallic Bi/Ni or Cu/Fe charge
 154 transfer transitions, whereas electrons released through the ionisation process $\text{R}^{2+} \rightarrow \text{R}^{3+} + \text{e}^-$
 155 in the R = Sm, Yb materials are delocalised in the conduction band at high temperatures. NTE
 156 in V_2OPO_4 where charge ordering occurs without a metal-insulator transition was recently
 157 reported [12].
- 158 • Orbital ordering transitions usually associated with first-order Jahn-Teller distortions give rise
 159 to NTE in several materials. Ca_2RuO_4 has orbital order associated with a metal-insulator
 160 transition, while insulating LaMnO_3 which is much studied as the parent phase of the
 161 perovskite manganites undergoes a 0.4 % cell volume decrease at 750 K where the orbital
 162 order-disorder transition occurs.
- 163 • Ferroelectrics associated with off-centre displacements of cations to give a net polarisation
 164 sometimes show NTE below their Curie transitions. Prominent examples are perovskite
 165 oxides of lead with transition metal cations showing a second-order Jahn-Teller effect such as
 166 PbTiO_3 , $\text{Pb}(\text{Mg}_{0.33}\text{Ta}_{0.67})\text{O}_3$, and $\text{Pb}(\text{Fe}_{0.5}\text{Nb}_{0.5})\text{O}_3$. Cooling below T_C leads to a change from
 167 symmetric $\text{O}-\text{M}-\text{O}-\text{M}-\text{O}$ to asymmetric $\text{O}\cdots\text{M}-\text{O}\cdots\text{M}-\text{O}$ chains of atoms leading to
 168 polarity in the chain direction. The lengthening of $\text{O}\cdots\text{M}$ bonds where electrons are localised
 169 in antibonding states outweighs the shortening of the M-O bonds, leading to a net expansion
 170 in the polar chain direction on cooling and hence the excess volume associated with NTE
 171 below T_C . This can lead to very large volume collapses on warming, for example,
 172 $\text{Pb}_{0.8}\text{Bi}_{0.2}\text{VO}_3$ shows $\Delta V/V = -7.9\%$ around $T_C \approx 600 \text{ K}$ [13].
- 173 • Superconductors sometimes show an excess volume and NTE below their critical
 174 temperatures T_c , for example in MgB_2 , $\text{La}_{1.85}\text{Sr}_{0.15}\text{CuO}_4$, and $\text{NdFeAsO}_{0.89}\text{F}_{0.11}$. Electron-

175 phonon coupling is directly implicated in the superconducting mechanism for BCS-type
 176 MgB_2 , whereas the latter two materials are unconventional superconductors where a magnetic
 177 pairing mechanism may be important. Loss of bonding electron density at the Fermi level due
 178 to electron-pairing below T_c is the general cause of NTE in superconductors.

179 Further details and citations when not shown above are given in the comprehensive review of NTE in
 180 functional materials by Chen et al [1].

181 **3 Morphological NTE**

182 The structural and electronic mechanisms for NTE described above apply to chemically homogenous
 183 materials such as a single crystal. However, there are further instances where NTE can arise or differ
 184 from the normal bulk behaviour due to the specific morphology of the sample.

185 **3.1 Nanoparticle NTE**

186 A variety of materials that show bulk PTE have been found to display NTE when prepared as small
 187 particles, usually in the nanoscale regime. For example, the magnetic insulators CuO and MnF_2 show
 188 PTE in the bulk but as 5 nm particles they display NTE below their Néel temperatures. CuO has a
 189 giant NTE of $\alpha_V = -110 \times 10^{-6} \text{ K}^{-1}$ between 20 and 170 K [14]. Nanoparticles of Au [15] and TiO_2
 190 [16] are also reported to display NTE.

191 The origin of nanoparticle NTE is usually electronic as, for example, the excess volume of CuO
 192 particles above follows the general behaviour shown in Fig. 4. Localisation of ordered or correlated
 193 states tends to be enhanced at and near surfaces so the associated lattice expansion on cooling can
 194 dominate the overall behaviour in small particles with a large proportion of surface atoms. The
 195 structural NTE mechanism could also play a part as surface atoms have a lower connectivity than the
 196 bulk so transverse vibrational amplitudes may be enhanced.

197 **3.2 Microstructural NTE**

198 Direct measurement of α_V for ceramic samples sometimes gives a more negative value than that
 199 expected from crystallographic measurement of the linear TECs. The excess negative expansion is
 200 achieved by reducing the volumes of microcracks or voids within the ceramic on heating, as
 201 illustrated schematically in Fig. 5. Microstructural NTE was reported in an early study of β -eucryptite
 202 (LiAlSiO_4) [17] and very large effects have recently been discovered in Ca_2RuO_4 [18]. These ceramic
 203 materials both have anisotropic thermal expansion with one strongly negative coefficient that
 204 dominates the expansion of their ceramics. For example, on heating from 150 to 340 K, the
 205 orthorhombic a , b , and c axes of Ca_2RuO_4 show length changes of -0.6 , -5.0 , and $+4.5\%$
 206 respectively, so an overall $\Delta V/V = -1.1\%$ is expected. However an 80% dense ceramic sample gave
 207 $\Delta V/V = -6.7\%$ revealing a substantial microstructural NTE effect.

208 Anisotropic thermal expansion leads to stresses at grain boundaries that result in microcracking in β -
 209 eucryptite ceramics on cooling to room temperature after sintering. Reduction of the microcrack
 210 volumes on subsequent heating results in bulk NTE and an enhancement of the excess NTE with
 211 increasing grain size (and hence internal microcrack volume) has been established [19]. However,
 212 this is less problematic for Ca_2RuO_4 -based ceramics, which have been combined with epoxy resin to
 213 generate ZTE materials that are stable to microcracking on thermal cycling [20].

214 **3.3 Metamaterials NTE**

215 Artificial structures consisting of two or more materials with different TECs (which may all be
216 positive) can be engineered to contract when heating. A simple example based on bonded strips of
217 two materials with different positive TECs is shown in Fig. 6. The structure contracts on heating
218 through reduction of the volume of internal voids, which outweighs the increase in volume of the
219 materials themselves. Designs for three-dimensional cellular metamaterials with varying TECs based
220 on the use of such bimaterial connectors were proposed by Lakes [21].

221 Recent developments in additive manufacturing through three-dimensional printing technologies have
222 enabled metamaterials with bulk NTE to be generated. In a recent example, a two-component polymer
223 metamaterial showed bulk negative expansion with $\alpha_L = -50 \times 10^{-6} \text{ K}^{-1}$ although the individual
224 components had PTE with an average $\alpha_L = 40 \times 10^{-6} \text{ K}^{-1}$ [22].

225 **4 Summary**

226 Although many diverse examples of NTE materials are reported, they may be classified according to
227 two types of intrinsic mechanism. Electronic NTE arises from reduction in first-neighbour distances
228 upon heating due to changes in the interatomic potential. These changes may arise from a variety of
229 physical property transitions such as magnetism, charge transfer, ferroelectricity and
230 superconductivity that alter the distribution of electron density. Structural NTE occurs through
231 reduction in second- or higher- neighbour distances upon heating due to dominant effects of
232 transverse vibrations such as bending or torsional modes, and is found in many framework-type
233 materials with a high proportion of 2-connected linkers.

234 The intrinsic NTE mechanisms may be enhanced in nanoparticles, most likely through electronic
235 effects from localisation of ordered or correlated states near surfaces. Further morphological
236 mechanisms for NTE of bulk artefacts result from reducing the volume of internal voids upon
237 heating. Microstructural NTE is found for ceramics of materials having anisotropic thermal
238 expansion coefficients. Artificial structures of substances with different expansion coefficients may
239 be used to generate metamaterials with NTE even when the individual components have PTE
240 behaviour.

241 **5 Conflict of Interest**

242 The author declares that the research was conducted in the absence of any commercial or financial
243 relationships that could be construed as a potential conflict of interest.

244 **6 Author Contributions**

245 This paper was written solely by the author.

246 **7 Funding**

247 The author acknowledges financial support from EPSRC.

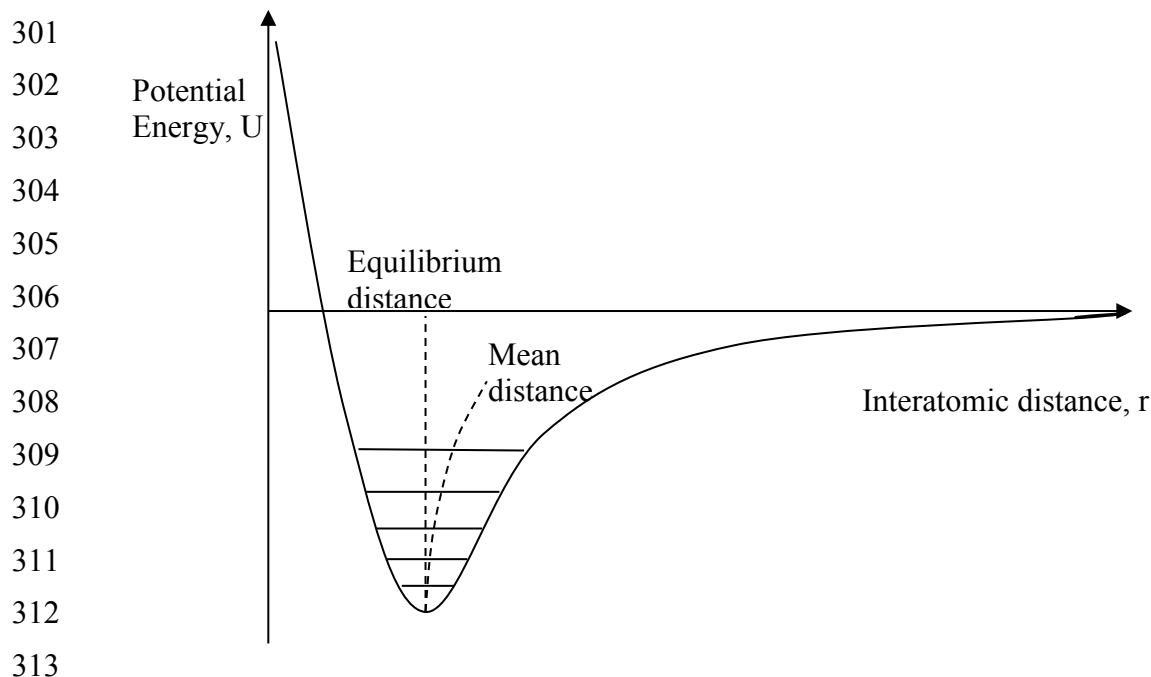
248 **8 Acknowledgments**

249 This paper is based upon a talk presented at the 2nd International Symposium on Negative Thermal
250 Expansion and Related Materials (ISNTE-II) at Tokyo Institute of Technology, Yokohama, Japan in
251 December 2017. The author thanks the organisers and participants for their contributions that helped
252 to shape the ideas presented in this paper.

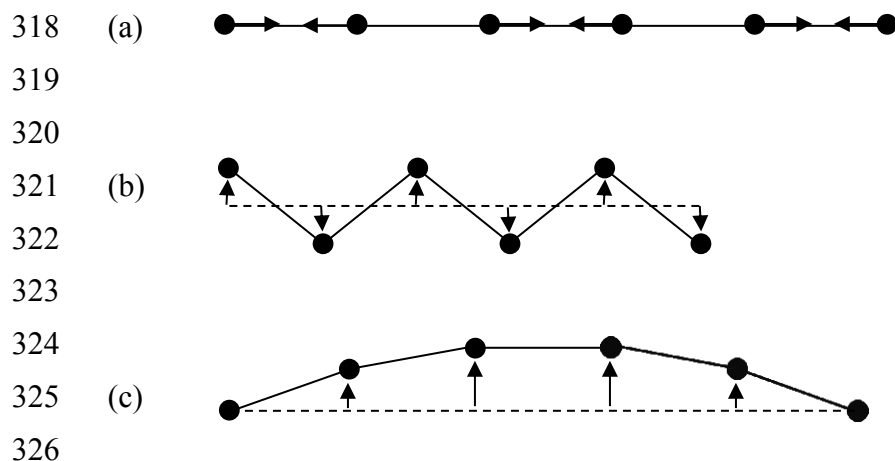
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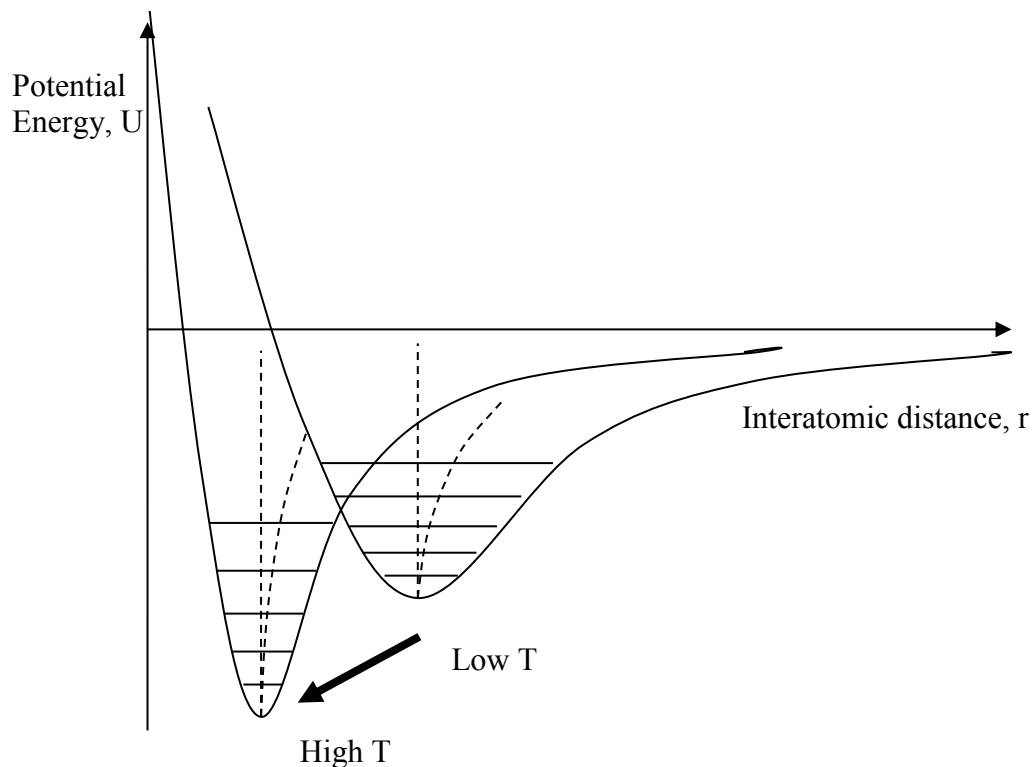
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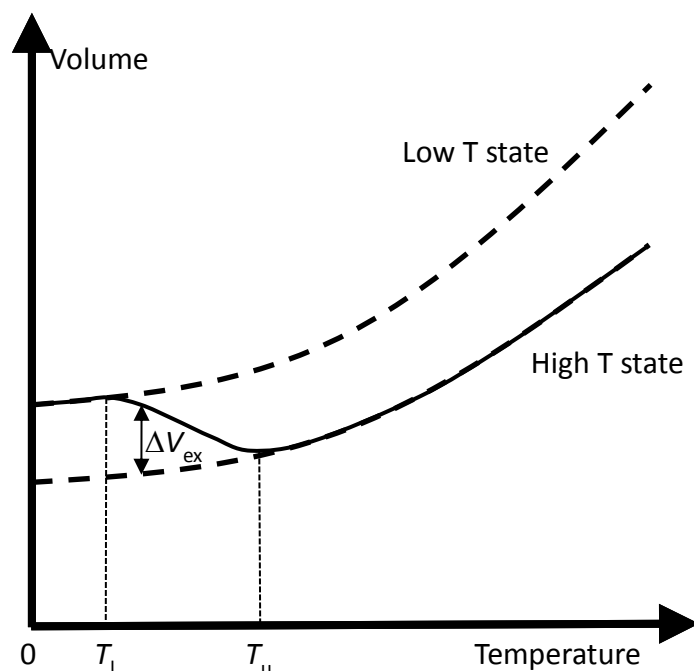
314 Fig. 1 The interatomic bonding potential, showing the variation of potential energy with interatomic
 315 distance for a pair of bonded atoms. Vibrational energy levels are quantised and with increasing
 316 temperature the occupation of higher levels leads to a slight increase in the mean interatomic distance
 317 relative to the minimum–energy equilibrium distance as shown.



327 Fig. 2 Schematic illustrations of lattice modes for a chain of atoms. (a) Longitudinal optic (LO) mode
 328 leading to PTE through asymmetry of the pairwise bonding potential shown in Fig. 1. (b) High energy
 329 transverse optic (TO) mode that greatly shortens the chain giving large NTE as the vibrational
 330 amplitude increases with temperature. (c) Low energy transverse acoustic (TA) mode leading to more
 331 modest NTE as temperature increases.



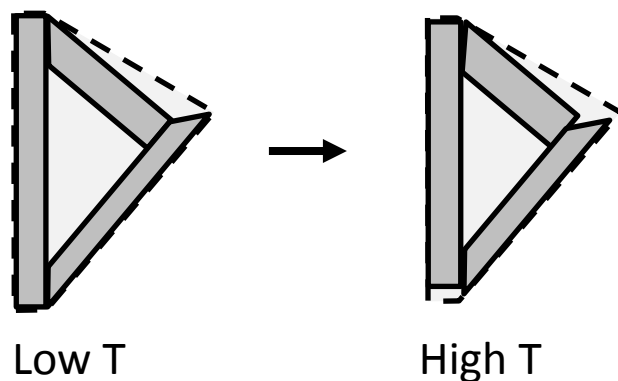
348 Fig. 3 Illustration of electronic mechanisms for NTE, where the interatomic bonding potential changes
 349 with temperature, moving to a more strongly bonding curve with smaller equilibrium distance at higher
 350 temperature. This may occur through a relatively sharp first order phase transition between two distinct
 351 states, or the potential may gradually evolve with changing temperature.



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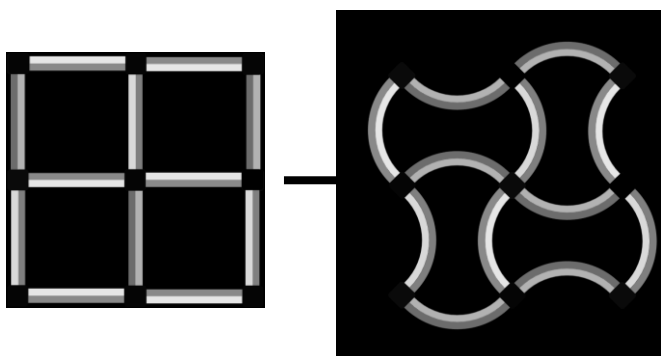
354 Fig. 4 Schematic changes in lattice volume with temperature for a material displaying electronic NTE.
355 The change from the larger-volume low- T to the smaller-volume high- T states (as shown in Fig. 3)
356 leads to NTE in the crossover region with lower and upper temperatures T_l and T_u . T_u often marks an
357 ordering temperature such as a magnetic or ferroelectric Curie transition. The electronically-induced
358 excess volume ΔV_{ex} relative to the extrapolated volume of the high- T state is shown

359



360

361 Fig. 5 Illustrative two-dimensional model for the microstructural NTE effect, showing three crystallites
362 enclosing a void. The crystallites shown have contracted by 10% along their long axis and expanded
363 by 10% in the perpendicular direction on changing from low T to high T , so their total area has not
364 changed. However, the enclosing area for the ensemble shown by broken lines undergoes an overall
365 decrease of 8%, illustrating how anisotropic thermal expansion may lead to overall NTE.

Low T High T

366

367 Fig. 6 Illustrative two-dimensional example of an NTE metamaterial consisting of a square lattice of
368 bimaterial strips acting as struts between 4-connected nodes. On heating from the low T to the high T
369 state, the light and dark grey materials respectively expand in length by 6 and 17%, but the separation
370 between nodes decreases by 4% corresponding to an 8% area contraction. Hence the metamaterial
371 consisting of only PTE substances shows bulk NTE.